Docket No. 12054-0023



DECLARATION AND POWER OF ATTORNEY

As a below named involver, I declare that:

My residence, post office address, and citizenship are as stated below next to my name. I believe that I am the original, first and sole inventor post of the subject matter that is claimed (if only one name is listed below) or an original, first, and joint inventor (if plural names are listed below) of the subject matter that is claimed • and for which a patent is sought on the invention entitled

HEAT TREATMENT JIG FOR SEMICONDUCTOR SUBSTRATE AND METHOD OF HEAT TREATING SEMICONDUCTOR SUBSTRATE

the specification of which is at Was filed on January 5, amended on		on Serial No. <u>10/750, 883</u>	, and (if applicable) was
hereby state that I have reviewed and unreferred to above.	derstand the contents of the above ident	tified specification, including the claims,	as amended by any amendment
I acknowledge the duty to disclose inform 37 CFR §1.56.	ation of which I am aware and which is	material to the examination of the patent	application in accordance with
I hereby claim foreign priority benefits und any PCT International application which checking the space, any foreign applicati application on which priority is not claimed	designates at least one country other to on for patent or inventor s certificate, or	han the United States, listed below and	have also identified below, by
Prior Foreign Application(s)			
Number	Country	Day/Month/Year Filed	Priority Not Claimed
2003-378724	JAPAN	07/11/2003	
The state of the s	8110(x) of IV-it -I Co. A	and looking (a) listed below	
I hereby claim the benefit under 35 U.S.C.	**		•
Application Ser	iai Number	Filing Date	
filing date of this application. Application Serial Number	Filing Date	Status (patented, pending, ab	andoned)
Each undersigned applicant hereby appoi 33,613), as his attorneys with full power of connected therewith.			
Send Correspondence to: CLARK & BR 835-1755.			
I hereby declare that all statements made here that these statements were made with the know of Title 18 of the United States Code and that	ledge that willful false statements and the lil	ke so made are punishable by fine or imprisor	nment, or both, under Section 1001
Full name of sole or first inventor: Inventor's signature: Residence: Tokyo, Japan Citizenship: Japan Post Office Address: do Sumito		Date: /9//	/2 <i>/ 2003</i> u, Tokyo 105-8634 Japan
Full name of second joint inventor, inventor's signature: Residence: Tokyo, Japan Citizenship: Japan	Kezuski Yokide		2 / 2003
Post Office Address: c/o Sumiton	o Mitsubishi Silicon Corporation,	2-1, Shibaura 1-chome, Minato-ku,	Tokyo 105-8634 Japan
	X third and subsequent joint inven	tors are listed on second sheet	

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Full name of third join	t inventor, if any: <u>Yospiro AOr</u>	<u> </u>			
Inventor's signature:	t inventor, if any: Yoshiro AUF	roki	Date:	21/12/2003	
Residence: Tokyo.	Japan 0				
Citizenship: Japan					
Post Office Address:_	c/o Sumitomo Mitsubishi Silico	on Corporation, 2-1, SI	<u>hibaura 1-chome, M</u>	<u>inato-ku, Tokyo 105-8634 J</u>	lapan
Full name of fourth joi	nt inventor, if any:				
Inventor's signature:			Date:		
-					
Citizenship:					
`					
	inventor, if any:				
•	•				
Posidones:	·				
7 05(011100 / (441000)					
Full name of sixth join	t inventor, if any:				
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